MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

# TPH7R506NH

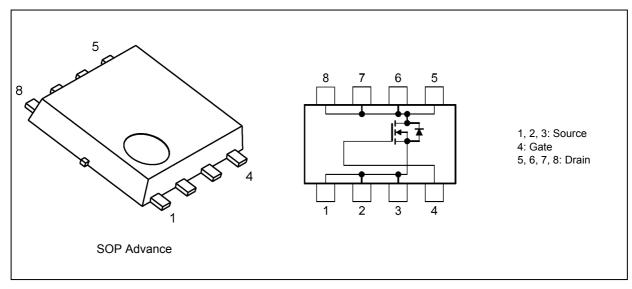
### 1. Applications

- Switching Voltage Regulators
- Motor Drivers
- DC-DC Converters

#### 2. Features

- (1) Small footprint due to a small and thin package
- (2) High-speed switching
- (3) Small gate charge:  $Q_{SW} = 14 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 6.1 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (5) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 60 \ V)$
- (6) Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.3 mA)

### 3. Packaging and Internal Circuit



# 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	60	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I <sub>D</sub>	55	A
Drain current (DC)		(Note 1)	Ι <sub>D</sub>	22	
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I <sub>DP</sub>	66	
Power dissipation	(T <sub>c</sub> = 25°C)		PD	45	W
Power dissipation	(t = 10 s)	(Note 3)	PD	2.8	w
Power dissipation	(t = 10 s)	(Note 4)	PD	1.6	w
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	132	mJ
Avalanche current			I <sub>AR</sub>	22	A
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics				Max	Unit
Channel-to-case thermal resistance	(T <sub>c</sub> = 25°C)		R <sub>th(ch-c)</sub>	2.78	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R <sub>th(ch-a)</sub>	44.6	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R <sub>th(ch-a)</sub>	78.1	°C/W

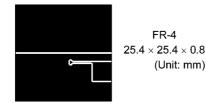
Note 1: Ensure that the channel temperature does not exceed 150°C.

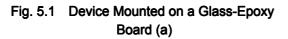
Note 2: Limited by silicon capability.

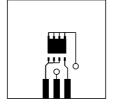
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V\_DD = 24 V, T\_ch = 25°C (initial), L = 0.38 mH, R\_G = 1  $\Omega$ , I\_AR = 22 A







 $\begin{array}{c} \text{FR-4}\\ \text{25.4}\times\text{25.4}\times\text{0.8}\\ \text{(Unit: mm)} \end{array}$ 

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

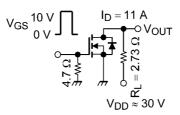
# 6.1. Static Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	_		10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	60	_	—	V
Drain-source breakdown voltage (Note 6)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	45	_	—	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.3 mA	2.0	_	4.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 6.5 V, I <sub>D</sub> = 11 A	_	8.2	19	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 11 A		6.1	7.5	

Note 6: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1 MHz		1785	2320	pF
Reverse transfer capacitance	C <sub>rss</sub>	]		40	80	
Output capacitance	C <sub>oss</sub>		_	575	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	1.0	1.5	Ω
Switching time (rise time)	tr	See Figure 6.2.1	_	9.4	—	ns
Switching time (turn-on time)	t <sub>on</sub>	1	_	21	—	
Switching time (fall time)	t <sub>f</sub>	]		7.3		
Switching time (turn-off time)	t <sub>off</sub>	]		25	_	



 $Duty \leq 1\%, \, t_W = 10 \ \mu s$ 

#### Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

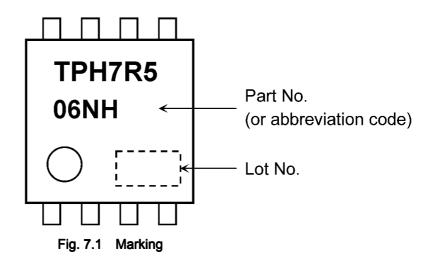
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 48$ V, $V_{GS}$ = 10 V, $I_D$ = 22 A	—	31	—	nC
Gate-source charge 1	Q <sub>gs1</sub>			9.5	—	
Gate-drain charge	Q <sub>gd</sub>		_	9.5	_	
Gate switch charge	Q <sub>SW</sub>			14	_	

# 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

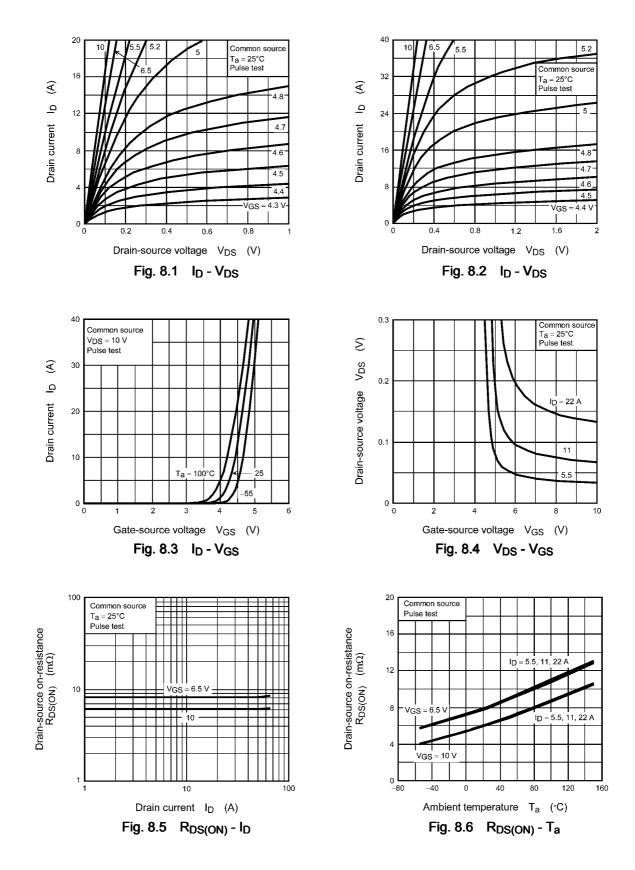
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note	7) I <sub>DRP</sub>	—	_	_	66	А
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 22 A, V <sub>GS</sub> = 0 V	—		-1.2	V

Note 7: Ensure that the channel temperature does not exceed 150°C.

# 7. Marking



# 8. Characteristics Curves (Note)



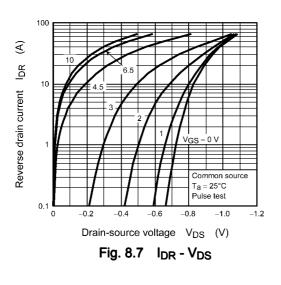
F

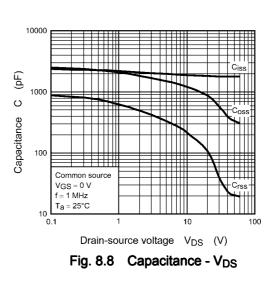
0

. --80

-40

0





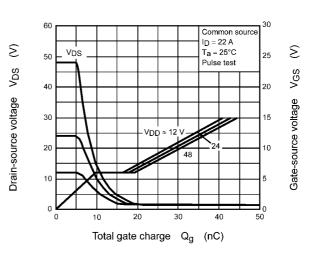
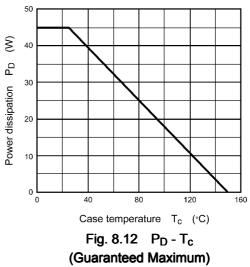
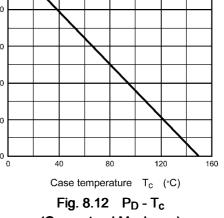


Fig. 8.10 Dynamic Input/Output Characteristics





S Gate threshold voltage 3 2 Common source VDS = 10 V  $I_{D} = 0.3 \text{ mA}$ Pulse test

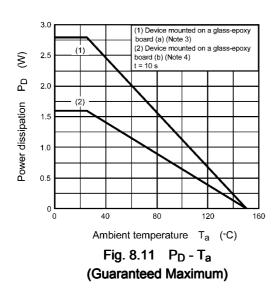
Ambient temperature Ta (°C) Fig. 8.9 V<sub>th</sub> - T<sub>a</sub>

40

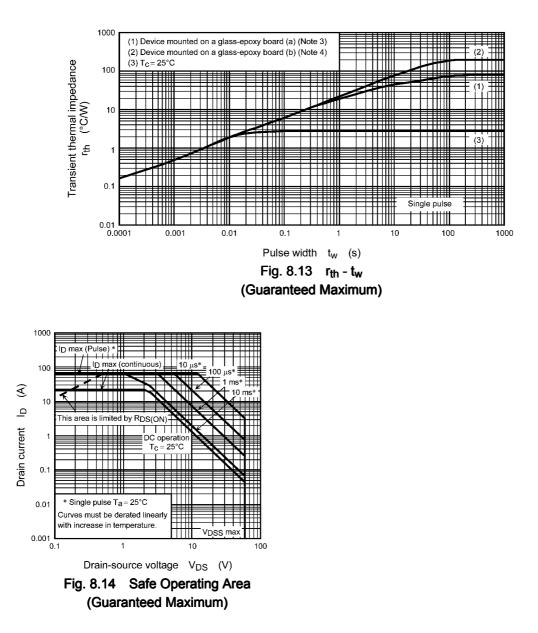
80

120

160







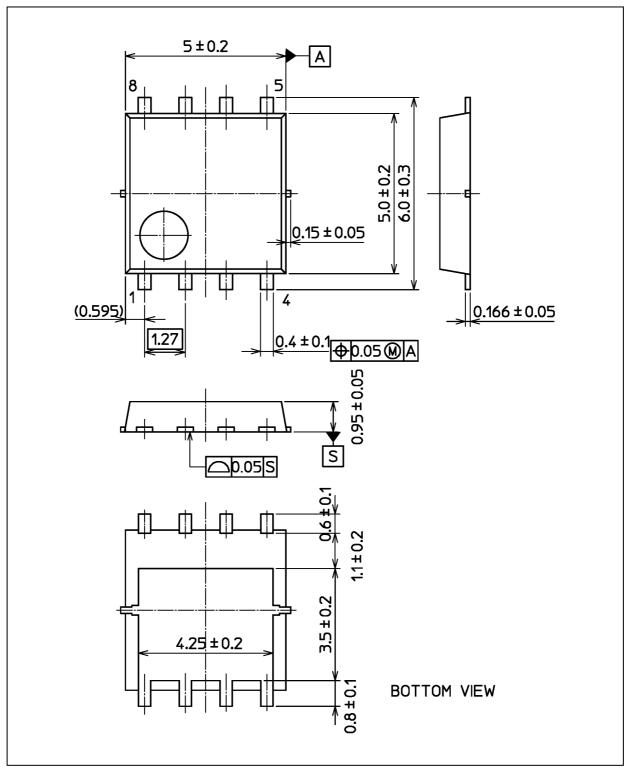
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# TPH7R506NH

# Package Dimensions

Unit: mm



#### Weight: 0.069 g (typ.)

Package Name(s)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

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